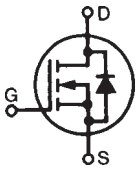
IXYS

PolarHV™ HiPerFET Power MOSFET

IXFK 64N60P
IXFX 64N60P

V_{DSS} = 600 V
I_{D25} = 64 A
$R_{DS(on)}$ ≤ 96 mΩ
t_{rr} ≤ 200 ns

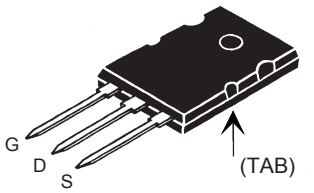
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



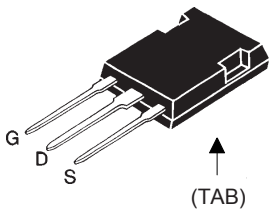
Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25° C to 150° C	600	V
V_{DGR}	T_J = 25° C to 150° C; R_{GS} = 1 MΩ	600	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25° C	64	A
I_{DM}	T_C = 25° C, pulse width limited by T_{JM}	150	A
I_{AR}	T_C = 25° C	64	A
E_{AR}	T_C = 25° C	80	mJ
E_{AS}	T_C = 25° C	3.5	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤100 A/μs, $V_{DD} \le V_{DSS}$, $T_J \le$150° C, R_G = 2 Ω	20	V/ns
P_D	T_C = 25° C	1040	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10 s	260	°C
F_C	Mounting force (PLUS247)	20..120/4.5..25	N/lb
M_d	Mounting torque (TO-264)	1.13/10	Nm/lb.in.
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions (T_J = 25° C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D = 3 mA	600			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8 mA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30 V_{DC}, V_{DS} = 0			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$			25	μA
	V_{GS} = 0 V, T_J = 125° C			1000	μA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5\ I_{D25}$, Note 1			96	mΩ

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

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Symbol	Test Conditions (T_J = 25° C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20 V; I_D = 0.5 I_{D25}, Note 1	40	63		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		12		nF
C_{oss}			1150		pF
C_{rss}			80		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D =0.5 I_{D25} R_G = 1 Ω (External)		28		ns
t_r			23		ns
$t_{d(off)}$			79		ns
t_f			24		ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		200		nC
Q_{gs}			70		nC
Q_{gd}			68		nC
R_{thJC}				0.12	°C/W
R_{thCS}			0.15		°C/W

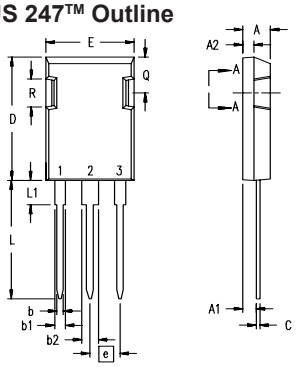
Source-Drain Diode

Symbol	Test Conditions (T_J = 25° C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0 V			64	A
I_{SM}	Repetitive			150	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Note 1			1.5	V
t_{rr}	I_F = 25A, -di/dt = 100 A/µs			200	ns
Q_{RM}	V_R = 100V		0.6		µC
I_{RM}			6.0		A

Notes:

1. Pulse test, t ≤300 µs, duty cycle d≤ 2 %

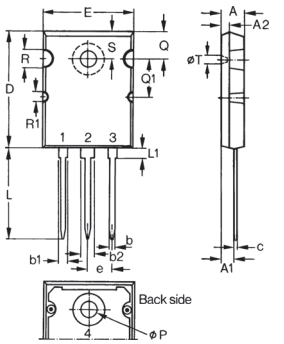
PLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

TO-264 Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or moreof the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405B2 6,710,463 6,727,585 6,759,692 6,771,478 B2

Fig. 1. Output Characteristics @ 25ºC

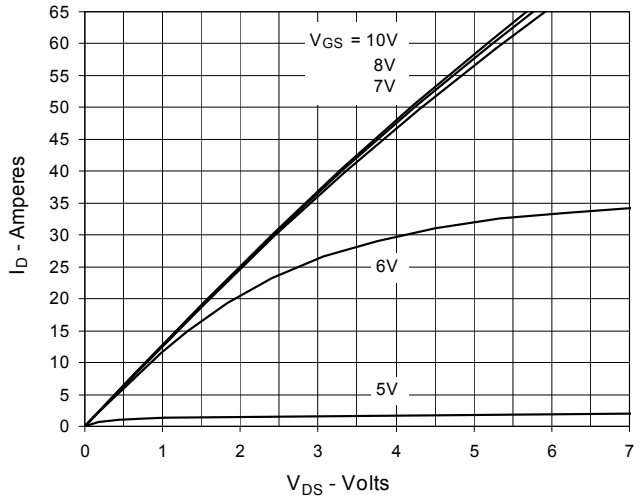


Fig. 2. Extended Output Characteristics @ 25ºC

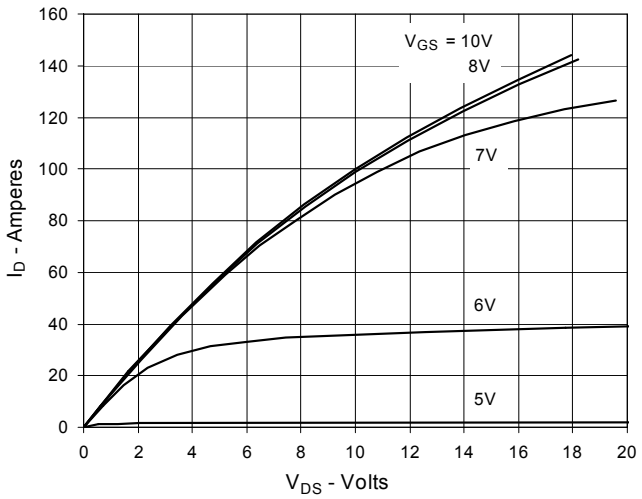


Fig. 3. Output Characteristics @ 125ºC

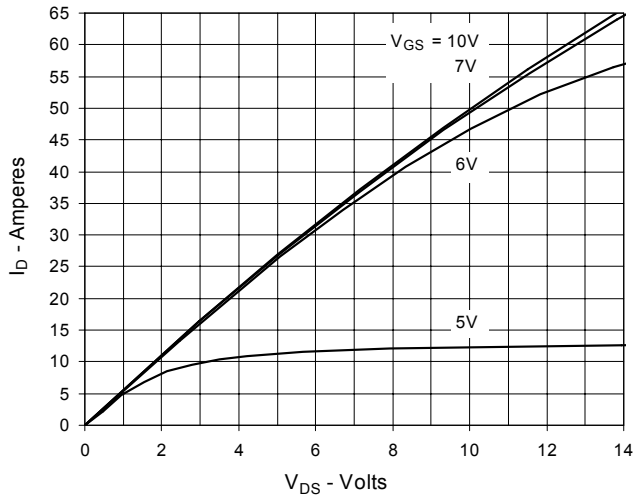


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 32A vs. Junction Temperature

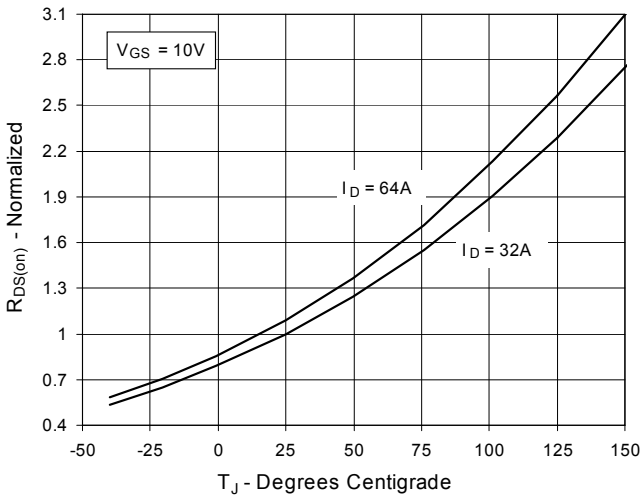


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 32A vs. Drain Current

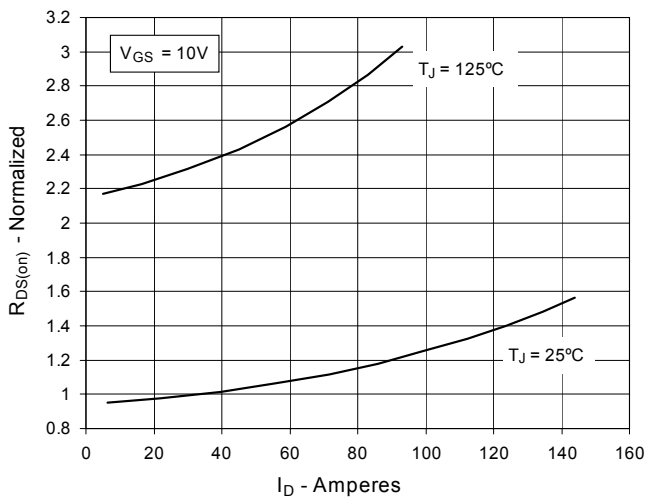
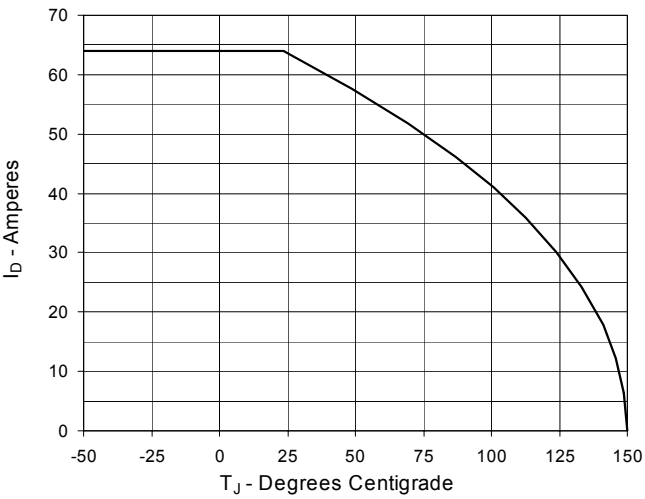


Fig. 6. Maximum Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

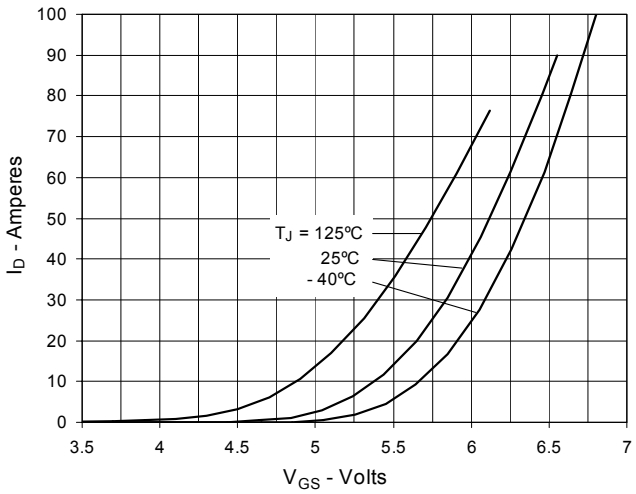


Fig. 8. Transconductance

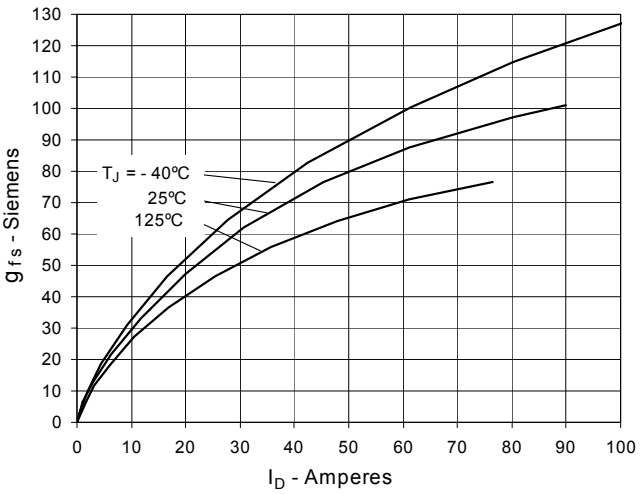


Fig. 9. Forward Voltage Drop of Intrinsic Diode

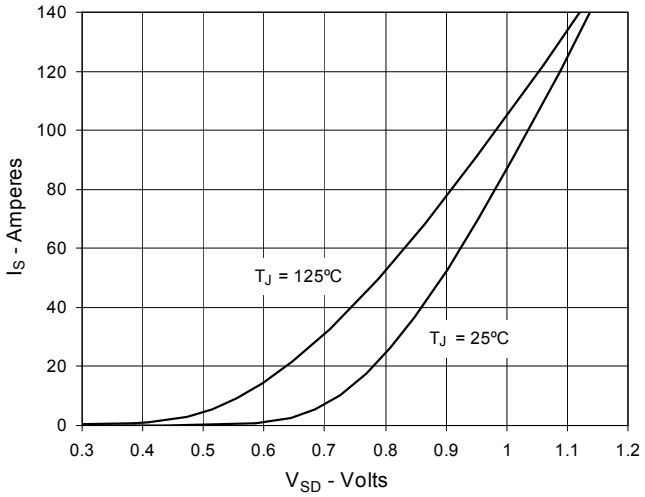


Fig. 10. Gate Charge

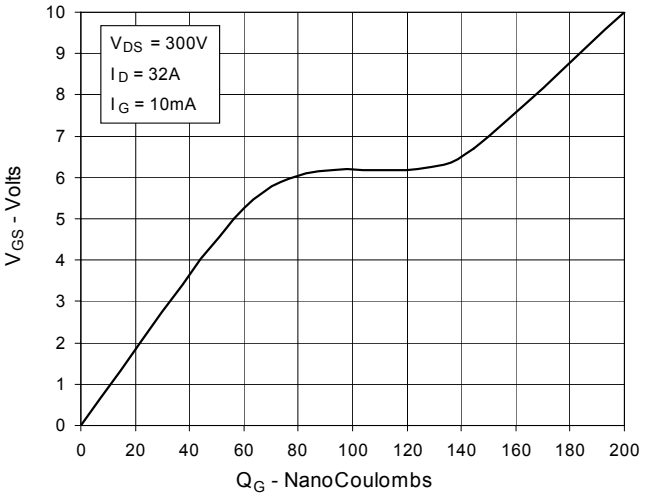


Fig. 11. Capacitance

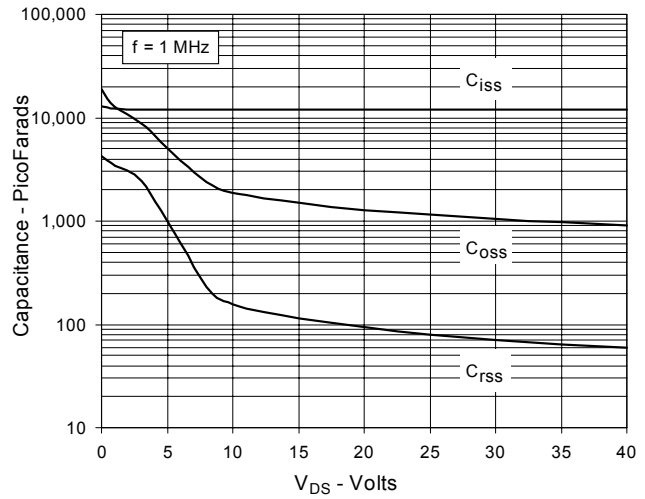
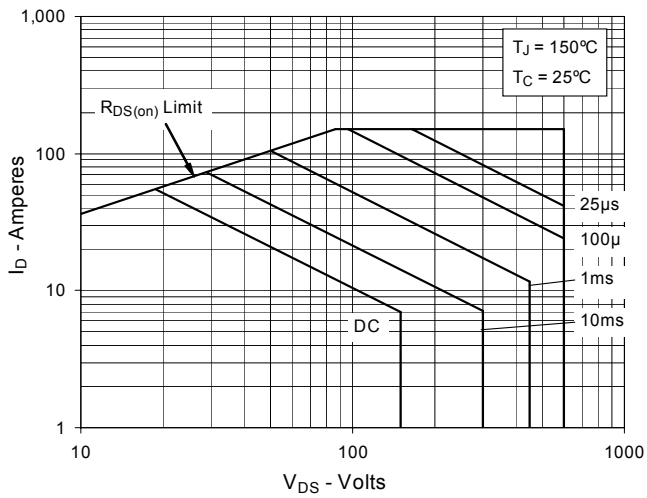
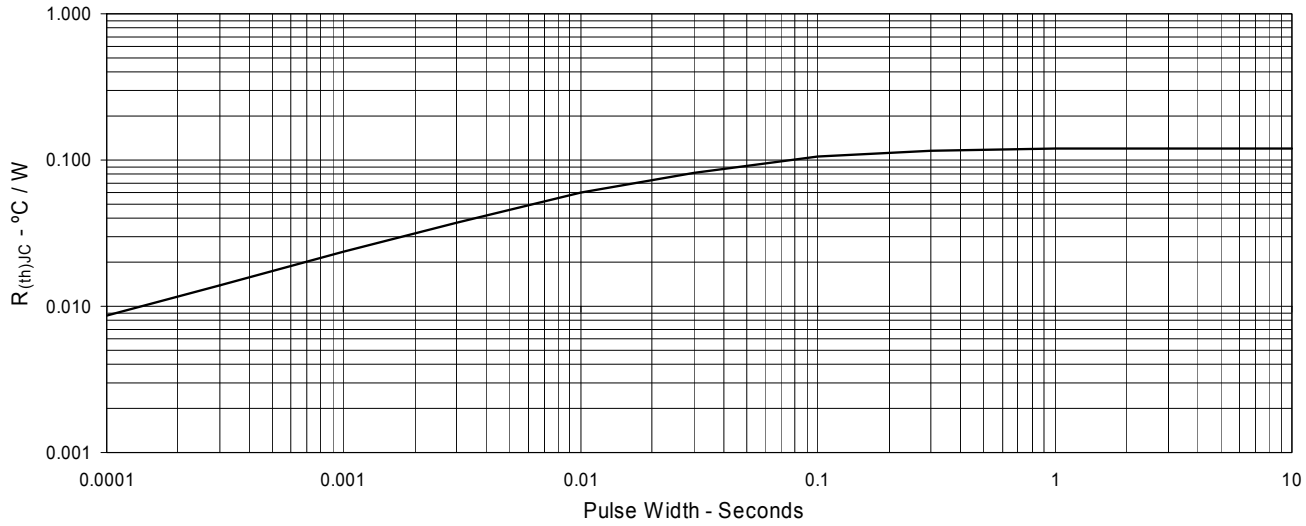


Fig. 12. Forward-Bias Safe Operating Area



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Fig. 13. Maximum Transient Thermal Resistance



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